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Synchronous 4-bit Binary Counter (Direct Clear)



ADE-205-264B (Z)

3rd. Edition Jul. 2001

Description

The HD74LV161A is 4-bit binary counters. All flip flops are clocked simultaneously on the low to high to transition (positive edge) of the clock input waveform. These counters may be preset using the load input. Presetting of all four flip flops is synchronous to the rising edge of clock. When load is held low counting is disabled and tha data on the A, B, C and D inputs is loaded into the counter on the rising edge clock. If the load input is taken high before the positive edge of clock the count operation will be unaffected.

Low-voltage and high-speed operation is suitable for the battery-powered products (e.g., notebook computers), and the low-power consumption extends the battery life.

Features

- $V_{cc} = 2.0 \text{ V}$ to 5.5 V operation
- All inputs V_{H} (Max.) = 5.5 V (@ V_{CC} = 0 V to 5.5 V)
- All outputs V_0 (Max.) = 5.5 V (@ V_{CC} = 0 V)
- Typical V_{OL} ground bounce < 0.8 V (@ V_{CC} = 3.3 V, Ta = 25°C)
- Typical V_{OH} undershoot > 2.3 V (@ V_{CC} = 3.3 V, Ta = 25°C)
- Output current $\pm 6 \text{ mA}$ (@V_{cc} = 3.0 V to 3.6 V), $\pm 12 \text{ mA}$ (@V_{cc} = 4.5 V to 5.5 V)

Function Table

Inputs					Output	s		
CLR	LOAD	ENP	ENT	CLK	QA	QB	QC	QD
L	Х	Х	Х	Х	L	L	L	L
Н	L	Х	Х	1	Α	В	С	D
Н	Н	Х	L	↑	No chai	nge		
Н	Н	L	Х	↑	No chai	nge		
Н	Н	Н	Н	↑	Count u	ıp		
Н	Х	Х	Х	\downarrow	No chai	nge		

Note: H: High level

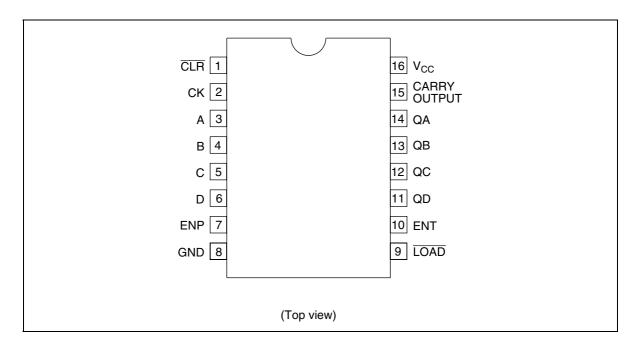
L: Low level

X: Immaterial†: Low to high transition

↓: High to low transition
 A, B, C, D: Data input

Carry = ENT • QA • QB • QC • QD

Pin Arrangement



Absolute Maximum Ratings

Item	Symbol	Ratings	Unit	Conditions
Supply voltage range	V _{cc}	-0.5 to 7.0	V	
Input voltage range*1	V _i	-0.5 to 7.0	V	H or L
Output voltage range*1,2	V _o	-0.5 to $V_{cc} + 0.5$	V	Output: H or L
		-0.5 to 7.0	=	V _{cc} : OFF
Input clamp current	I _{IK}	-20	mA	V ₁ < 0
Output clamp current	I _{ok}	±50	mA	$V_o < 0 \text{ or } V_o > V_{cc}$
Continuous output current	I _o	±25	mA	$V_o = 0$ to V_{cc}
Continuous current through V_{cc} or GND	I _{CC} or I _{GND}	±50	mA	
Maximum power dissipation at Ta = 25 °C (in still air)* ³	P _T	785	mW	SOP
		500	_	TSSOP
Storage temperature	Tstg	-65 to 150	°C	

Notes: The absolute maximum ratings are values which must not individually be exceeded, and furthermore, no two of which may be realized at the same time.

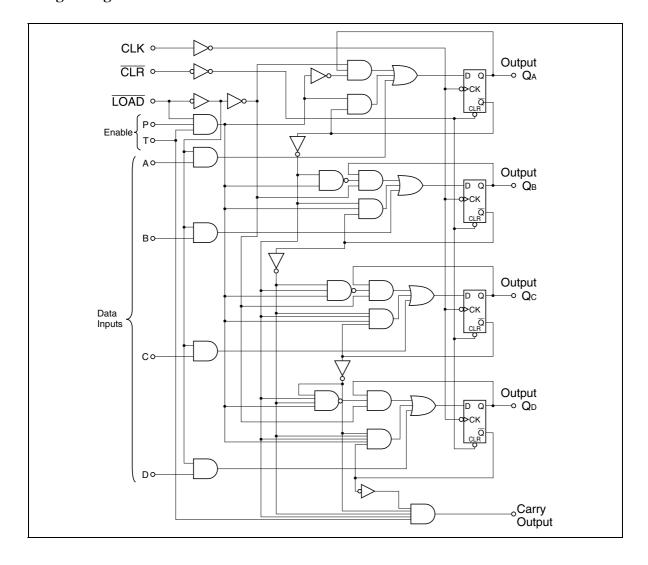
- 1. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
- 2. This value is limited to 5.5 V maximum.
- 3. The maximum package power dissipation was calculated using a junction temperature of 150°C.

Recommended Operating Conditions

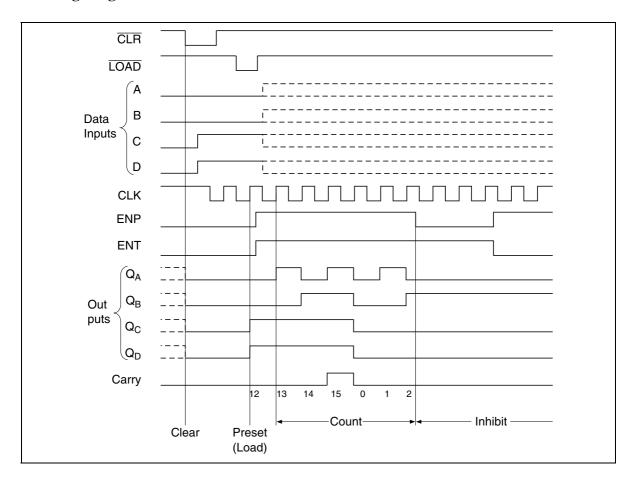
Item	Symbol	Min	Max	Unit	Conditions
Supply voltage range	V _{cc}	2.0	5.5	V	
Input voltage range	V _i	0	5.5	V	
Output voltage range	V _o	0	V _{cc}	V	
Output current	I _{OH}	_	-50	μΑ	$V_{cc} = 2.0 \text{ V}$
		_	-2	mA	$V_{cc} = 2.3 \text{ to } 2.7 \text{ V}$
		_	-6		$V_{cc} = 3.0 \text{ to } 3.6 \text{ V}$
		_	-12		$V_{cc} = 4.5 \text{ to } 5.5 \text{ V}$
	I _{OL}	_	50	μΑ	V _{cc} = 2.0 V
		_	2	mA	$V_{cc} = 2.3 \text{ to } 2.7 \text{ V}$
		_	6		$V_{cc} = 3.0 \text{ to } 3.6 \text{ V}$
		_	12		$V_{cc} = 4.5 \text{ to } 5.5 \text{ V}$
Input transition rise or fall rate	Δt /Δν	0	200	ns/V	$V_{cc} = 2.3 \text{ to } 2.7 \text{ V}$
		0	100		$V_{cc} = 3.0 \text{ to } 3.6 \text{ V}$
		0	20		$V_{cc} = 4.5 \text{ to } 5.5 \text{ V}$
Operating free-air temperature	Та	-40	85	°C	

Note: Unused or floating inputs must be held high or low.

Logic Diagram



Timing Diagram



DC Electrical Characteristics

 $Ta = -40 \text{ to } 85^{\circ}\text{C}$

Item	Symbol	V _{cc} (V)*	Min	Тур	Max	Unit	Test Conditions
Input voltage	V _{IH}	2.0	1.5	_	_	٧	
		2.3 to 2.7	$V_{cc} \times 0.7$	_	_	_	
		3.0 to 3.6	$V_{cc} \times 0.7$	_	_	_	
		4.5 to 5.5	$V_{cc} \times 0.7$	_	_	_	
	V _{IL}	2.0	_	_	0.5	_	
		2.3 to 2.7	_	_	$V_{cc} \times 0.3$	_	
		3.0 to 3.6	_	_	$V_{cc} \times 0.3$	_	
		4.5 to 5.5	_	_	$V_{cc} \times 0.3$	_	
Output voltage	V _{OH}	Min to Max	V _{cc} - 0.1	_	_	V	$I_{oL} = -50 \mu A$
		2.3	2.0	_	_	_	I _{OL} = -2 mA
		3.0	2.48	_	_		I _{OL} = -6 mA
		4.5	3.8	_	_	_	I _{oL} = -12 mA
	V _{OL}	Min to Max	_	_	0.1	_	Ι _{οι} = 50 μΑ
		2.3	_	_	0.4	_	I _{OL} = 2 mA
		3.0	_	_	0.44	_	I _{OL} = 6 mA
		4.5	_	_	0.55	_	I _{OL} = 12 mA
Input current	I _{IN}	0 to 5.5	_	_	±1	μΑ	$V_{IN} = 5.5 \text{ V or GND}$
Quiescent supply current	I _{cc}	5.5	_	_	20	μА	$V_{IN} = V_{CC}$ or GND, $I_{O} = 0$
Output leakage current	OFF	0	_	_	5	μΑ	$V_{_{\rm I}}$ or $V_{_{\rm O}}$ = 0 V to 5.5 V
Input capacitance	C _{IN}	3.3	_	1.7	_	pF	$V_{I} = V_{CC}$ or GND

Note: For conditions shown as Min or Max, use the appropriate values under recommended operating conditions.

Switching Characteristics

 $V_{cc} = 2.5 \pm 0.2 \text{ V}$

		Ta = 25°C		Ta = -	40 to 85°C					
Item	Symbol	Min	Тур	Max	Min	Max	Unit	Test Conditions	FROM (Input)	TO (Output)
Maximum clock frequency	fmax	50	90	_	40	_	MHz	C _L = 15 pF		
		30	60	_	25	_	_	C _L = 50 pF	=	
Propa- gation delay time	$t_{_{\mathrm{PLH}}}/t_{_{\mathrm{PHL}}}$	_	11.1	16.2	1.0	19.5	ns	C _L = 15 pF	CLK	Q
		_	14.3	19.2	1.0	22.5	=	C _L = 50 pF	=	
	t _{PLH} /t _{PHL}	_	11.5	17.0	1.0	20.5	-	C _L = 15 pF	CLK	Carry
	Count mode	_	14.7	20.0	1.0	23.5	_	C _L = 50 pF	-	
	t _{PLH} /t _{PHL}	_	13.8	20.6	1.0	24.5	-	C _L = 15 pF	CLK	Carry
	Load mode	_	17.0	23.6	1.0	27.5	_	C _L = 50 pF	-	
	t _{PLH} /t _{PHL}	_	10.3	15.7	1.0	19.0	_	C _L = 15 pF	ENT	Carry
		_	14.0	18.7	1.0	22.0	_	C _L = 50 pF		
	t _{PHL}	_	11.7	17.0	1.0	20.5	_	C _L = 15 pF	CLR	Q
		_	14.7	20.0	1.0	23.5	_	C _L = 50 pF		
	$t_{_{PHL}}$	_	11.2	16.6	1.0	20.0	=	C _L = 15 pF	CLR	Carry
		_	14.4	19.6	1.0	23.0		C _L = 50 pF		
Setup time	\mathbf{t}_{su}	7.5	_	_	8.5	_	ns		Data befor	e CLK↑
		10.0	_	_	11.5		_		LOAD before	ore CLK ↑
		9.5	_	_	11.0	_	_		ENT, ENP ↑	before CLK
		4.5			4.5				CLR inacti	ve before
Hold time	t _h	1.5	_	_	1.5	_	ns			
Pulse width	t _w	7.0	_	_	7.0	_	ns		CLK H or I	L
		7.0	_	_	7.0	_	_		CLR L	

Switching Characteristics (cont)

 $V_{cc} = 3.3 \pm 0.3 \text{ V}$

	Symbol	Ta = 25°C		Ta = -	Ta = -40 to 85°C					
Item		Min	Тур	Max	Min	Max	Unit	Test Conditions	FROM (Input)	TO (Output)
Maximum clock frequency	fmax	80	130	_	70	_	MHz	C _L = 15 pF		
		55	85	_	50	_	_	C _L = 50 pF	_	
Propa- gation delay time	$t_{_{PLH}}/t_{_{PHL}}$	_	8.3	12.8	1.0	15.0	ns	C _L = 15 pF	CLK	Q
-		_	10.8	16.3	1.0	18.5	_	C _L = 50 pF		
	t _{PLH} /t _{PHL}	_	8.7	13.6	1.0	16.0	_	C _L = 15 pF	CLK	Carry
	Count mode	_	11.2	17.1	1.0	19.5	_	C _L = 50 pF	_	
	t _{PLH} /t _{PHL}	_	11.0	17.2	1.0	20.0	_	C _L = 15 pF	CLK	Carry
	Load mode	_	13.5	20.7	1.0	23.5	_	C _L = 50 pF	_	
	$t_{\scriptscriptstyle PLH}/t_{\scriptscriptstyle PHL}$	_	7.5	12.3	1.0	14.5	_	C _L = 15 pF	ENT	Carry
		_	10.5	15.8	1.0	18.0	_	C _L = 50 pF		
	t _{PHL}	_	8.9	13.6	1.0	16.0	_	C _L = 15 pF	CLR	Q
		_	11.2	17.1	1.0	19.5	_	C _L = 50 pF		
	$\mathbf{t}_{_{\mathrm{PHL}}}$	_	8.4	13.2	1.0	15.5	_	C _L = 15 pF	CLR	Carry
		_	10.9	16.7	1.0	19.0		$C_L = 50 \text{ pF}$		
Setup time	\mathbf{t}_{su}	5.5	_	_	6.5	_	ns		Data befor	e CLK ↑
		8.0	_	_	9.5	_	_		LOAD before	ore CLK ↑
		7.5	_	_	9.0	_	_		ENT, ENP ↑	before CLK
		2.5	_	_	2.5	_	_		CLR inacti	ve before
Hold time	t _h	1.0	_	_	1.0	_	ns			
Pulse width	t _w	5.0	_	_	5.0	_	ns		CLK H or I	_
		5.0	_	_	5.0	_	=		CLR L	

Switching Characteristics (cont)

 $V_{cc} = 5.0 \pm 0.5 \text{ V}$

	Symbol	Ta = 25°C		Ta = -	Ta = −40 to 85°C					
Item		Min	Тур	Max	Min	Max	Unit	Test Conditions	FROM (Input)	TO (Output)
Maximum clock frequency	fmax	135	185	_	115	_	MHz	C _L = 15 pF		
		95	125	_	85	_	-	C _L = 50 pF	_	
Propagation delay time	$t_{_{\mathrm{PLH}}}/t_{_{\mathrm{PHL}}}$	_	4.9	8.1	1.0	9.5	ns	C _L = 15 pF	CLK	Q
		_	8.7	10.1	1.0	11.5	=	C _L = 50 pF	_	
	t _{PLH} /t _{PHL}	_	4.9	8.1	1.0	9.5	=	C _L = 15 pF	CLK	Carry
	Count mode	_	6.4	10.1	1.0	11.5	_	C _L = 50 pF	_	
	t _{PLH} /t _{PHL}	_	6.2	10.3	1.0	12.0	_	C _L = 15 pF	CLK	Carry
	Load mode	_	7.7	12.3	1.0	14.0	_	C _L = 50 pF	_	
	t _{PLH} /t _{PHL}	_	4.9	8.1	1.0	9.5	=	C _L = 15 pF	ENT	Carry
		_	6.4	10.1	1.0	11.5	_	C _L = 50 pF	_	
	t _{PHL}	_	5.5	9.0	1.0	10.5	_	C _L = 15 pF	CLR	Q
		_	7.0	11.0	1.0	12.5	_	C _L = 50 pF		
	t _{PHL}	_	5.0	8.6	1.0	10.0	_	C _L = 15 pF	CLR	Carry
		_	6.5	10.6	1.0	12.0	_	C _L = 50 pF		
Setup time	t _{su}	4.5	_	_	4.5	_	ns		Data befor	e CLK ↑
		5.0	_	_	6.0	_	_		LOAD before	ore CLK ↑
		5.0	_	_	6.0	_	_		ENT, ENP	before CLK
		1.5	_	_	1.5	_	_		CLR inacti	ve before
Hold time	t _h	1.0	_	_	1.0	_	ns			
Pulse width	t _w	5.0	_	_	5.0	_	ns		CLK H or I	L
		5.0	_	_	5.0	_	=		CLR L	

Operating Characteristics

 $C_L = 50 \text{ pF}$

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Item	Symbol	V_{cc} (V)	Min	Тур	Max	Unit	Test Conditions
Power dissipation capacitance	C_{\scriptscriptstylePD}	3.3	_	17.0	_	pF	f = 10 MHz
		5.0	_	20.4	_		

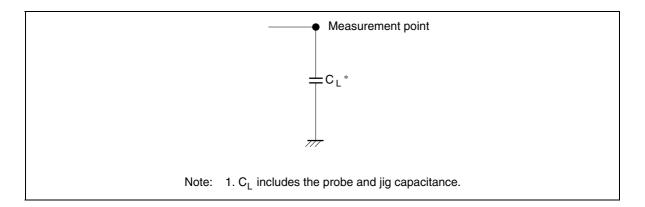
Noise Characteristics

 $C_L = 50 \text{ pF}$

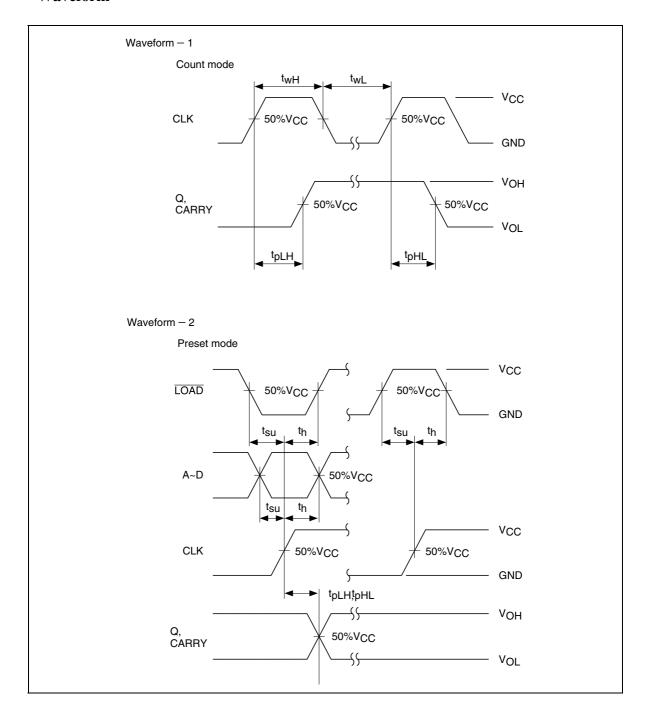
Ta	_	25	°C.

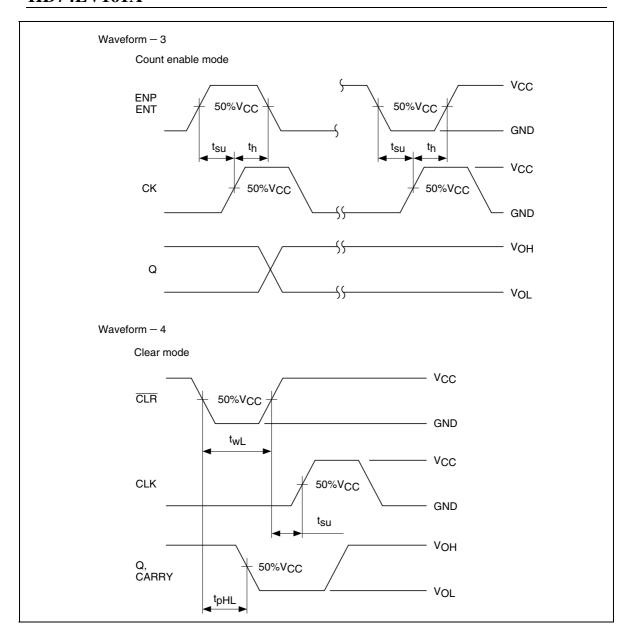
Item	Symbol	V_{cc} (V)	Min	Тур	Max	Unit	Test Conditions
Quiet output, maximum dynamic V _{oL}	$V_{_{OL(P)}}$	3.3	_	0.3	0.8	V	
Quiet output, minimum dynamic V _{oL}	V _{OL (V)}	3.3	_	-0.3	-0.8		
Quiet output, minimum dynamic V _{OH}	$V_{OH(V)}$	3.3	_	3.0	_		
High-level dynamic input voltage	$V_{_{IH\;(D)}}$	3.3	2.31	_	_	V	_
Low-level dynamic input voltage	V _{IL (D)}	3.3	_	_	0.99		

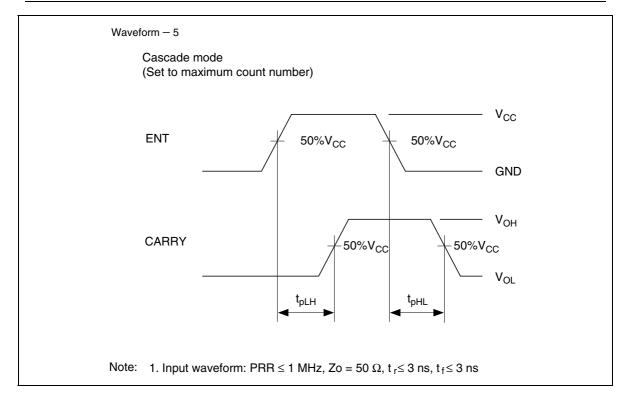
Test Circuit



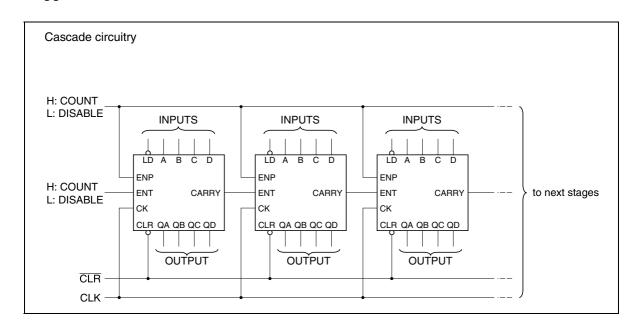
Waveform



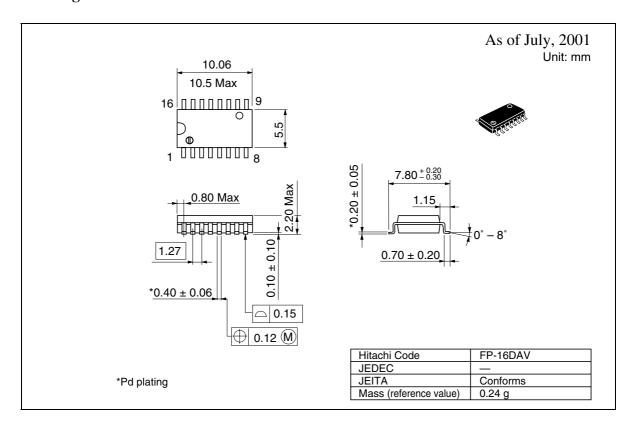


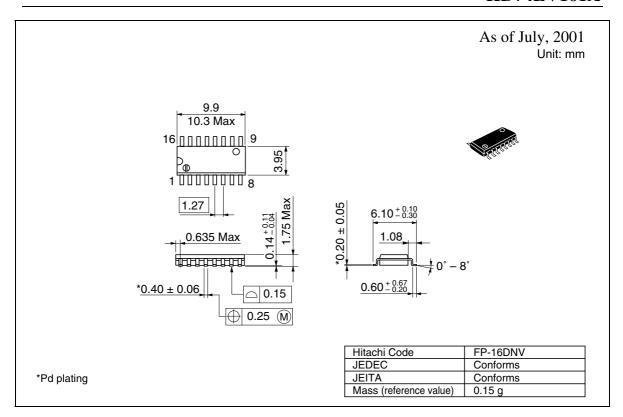


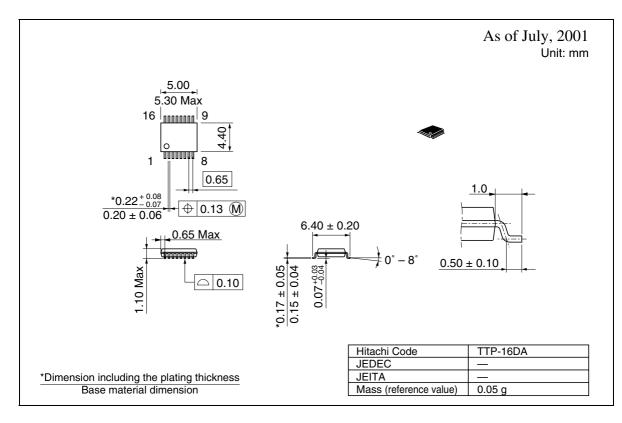
Application



Package Dimensions







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